TSMC-01-195CC

HAY 1 9 2004 WE CO

May 11, 2004

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Fr: George O. Saile, Reg. No. 19,572 28 Davis Avenue Poughkeepsie, N.Y. 12603

Subject:

Serial No. 10/823,149 04/13/04

Lain-Jong Li et al.

COMPOSITE ETCHING STOP IN SEMI-CONDUCTOR PROCESS INTEGRATION

INFORMATION DISCLOSURE STATEMENT

Enclosed is Form PTO-1449, Information Disclosure Citation In An Application.

The following Patents and/or Publications are submitted to comply with the duty of disclosure under CFR 1.97-1.99 and 37 CFR 1.56.

CERTIFICATE OF MAILING

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on May 17, 2004.

Stephen B. Ackerman, Reg.# 37761

Signature/Date

TSMC-01-195CC

- U.S. Patent 6,127,262 to Huang et al., "Method and Apparatus for Depositing an Etch Stop Layer," discloses a process for an etch stop layer.
- U.S. Patent 6,209,484 to Huang et al., "Method and Apparatus for Depositing an Etch Stop Layer," discloses a process for an etch stop layer.
- U.S. Patent 5,585,304 to Hayashi et al., "Method of Making Semiconductor Device with Multiple Transparent Layers," discusses a semiconductor wafer which is comprised of a transparent layer interposed between a thin silicon layer and a thick silicon layer.

Sincerely,

Stephen B. Ackerman,

Req. No. 37761

												J110 41	Lof		
orm 12	E	9								TSMC-01-195CC 10/823,149					
INFO	RM		IC	W W	DI	SC		OSURE C	Appaleuni	. 7 1. + 1.					
MAY 19	2004 (Us	ZE =) 	AIN (d)	.H she	ets i	il ne	CATION COSSESSORY)		Fring Own 04/13/04 Group in Unit					
PANE)	ARK	3 /							U. S. PATE	NT DOCUMENTS	7		· · · · · · · · · · · · · · · · · · ·	<u>·</u>	
REMINAZE	00	DOCUMENT HUMBER DATE						DATE		CLASS	MECTAL	AUNO	DATE		
	-	5585304						1 WITH 6	Hayoshi et al.				~/	- ALL	
	1		-	\vdash	T	✝	1	1 1	11 Jugash	t et al.	437	62	31-174		
	6	† <u>`</u>	2	П	П	П	Г	10/3/00	Ituang	elal.	4 38	634	5/1	197	
· · · · · · · · · · · · · · · · · · ·	9	2	0	9	14	8	14	4/3/01	Huana	et al.	118	723E	4/1	7/00	
	-	-	ŀ	-	\vdash	-	_	. '							
	_	igdash	_	_	L	-	_								
	_														
·						_									
					İ										
•										·					
				T	1		T			<u> </u>			, .		
		٠	<u>l:</u>	ـــــ	1_		ــــــــــــــــــــــــــــــــــــــ		FOREIGN PA	TENT DOCUMENTS	1	L	· ·		
	DOCUMENT NUMBER						3	DATE	cou	YRTN	cuss	SUBCLASS	Translation YES NO		
					Γ					······································	· ·			- 1~	
					-		-			· · · · · · · · · · · · · · · · · · ·				<u> </u>	
	\vdash		-	\vdash	-	-	-					-	} :- 		
			-	-	-	-	-					-			
	-		_	-	-	-	-		• • • • • • • • • • • • • • • • • • • •						
		_	Ŀ			_ '	_		· · · · · · · · · · · · · · · · · · ·						
OTHER DOCUMENTS (Induding Author, Title, Date, Pertinera Pages, Etc.)														.)	
	-													······································	
·		_		•			_		******	~~~			 -		
	-	_						·		· · · · · · · · · · · · · · · · · · ·					
												····			
REMAKASE										DATE CONMIDERED					
													•		
EVALOUE). T					_		• • • • •					· · · · · · · · · · · · · · · · · · ·		
citation it uc	cin:	cou	ılo 1 11	un:	anc au	c ou	nd nd	nsicer∞d, wh not conside	ictbor or not citati red. Include conv	ion is in conformance with of this form with next co.	nMPEP § (mmunicatio	509; Draw li on to the nor	ne throug	gb	
															